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From 1964 to the present, he has been a member of the Research Staff of the Ioffe Institute. His major professional achievements include: 1) Creation of the world's first ideal heterojunctions and low threshold double heterostructure lasers based on AlAs-GaAs solid solutions (1968, together with Zh.I. Alferov et al.). 2) Elaboration of the physical and technological principles of integrated optics based on heterostructures and creation of new integrated optical devices, including grating coupled surface emitting lasers and picosecond optical pulse generators.

He is currently Head of the Integrated Optics Laboratory at the Ioffe Institute and visiting professor at the Department of Electronics and Electrical Engineering the University of Glasgow.